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SuperSOT[™]-3

В

NPN Low Saturation Transistor

These devices are designed with high current gain and low saturation voltage with collector currents up to 3A continuous. Sourced from Process NC.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	FSB649	Units
VCEO	Collector-Emitter Voltage	25	V
V _{CBO}	Collector-Base Voltage	35	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current - Continuous	3	Α
T _{J,} T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150°C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

$\label{eq:TA} Thermal Characteristics \qquad T_{A=25^\circ C \text{ unless otherwise noted}}$

Symbol	Characteristic	Мах	Units
		FSB649	
PD	Total Device Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	°C/W

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Parameter	Test Conditions	Min	Max	Units
RACTERISTICS				
Collector-Emitter Breakdown Voltage	I _C = 10 mA	25		V
Collector-Base Breakdown Voltage	I _C = 100 μA	35		V
Emitter-Base Breakdown Voltage		5		V
Collector Cutoff Current	$V_{CB} = 30 V$ $V_{CB} = 30 V$, $T_{A} = 100^{\circ}C$		100 10	nA uA
Emitter Cutoff Current	V _{EB} = 4V		100	nA
				1
DC Current Gain	$I_{C} = 50 \text{ mA}, V_{CE} = 2 \text{ V}$ $I_{C} = 1 \text{ A}, V_{CE} = 2 \text{ V}$ $I_{C} = 2 \text{ A}, V_{CE} = 2 \text{ V}$ $I_{C} = 6 \text{ A}, V_{CE} = 2 \text{ V}$	70 100 75 15	300	-
Collector-Emitter Saturation Voltage	$I_{C} = 1 \text{ A}, I_{B} = 100 \text{ mA}$ $I_{C} = 3 \text{ A}, I_{B} = 300 \text{ mA}$		300 600	mV
Base-Emitter Saturation Voltage	I _C = 1 A, I _B = 100 mA		1.25	V
Base-Emitter On Voltage	I _C = 1 A, V _{CE} = 2 V		1	V
Output Capacitance	VcB = 10 V. IF = 0, f = 1MHz		50	pF
Transition Frequency		150		-
	ACTERISTICS Collector-Emitter Breakdown Voltage Collector-Base Breakdown Voltage Emitter-Base Breakdown Voltage Collector Cutoff Current Emitter Cutoff Current ACTERISTICS* DC Current Gain Collector-Emitter Saturation Voltage Base-Emitter On Voltage Base-Emitter On Voltage GNAL CHARACTERISTICS Output Capacitance	RACTERISTICSCollector-Emitter Breakdown Voltage $I_{C} = 10 \text{ mA}$ Collector-Base Breakdown Voltage $I_{C} = 100 \mu$ AEmitter-Base Breakdown Voltage $I_{E} = 100 \mu$ ACollector Cutoff Current $V_{CB} = 30 \text{ V}$ VCB = 30 V, T_A=100°CVEmitter Cutoff Current $V_{EB} = 4V$ ACTERISTICS*DC Current Gain $I_{C} = 50 \text{ mA}, V_{CE} = 2 \text{ V}$ $I_{C} = 1 \text{ A}, V_{CE} = 2 \text{ V}$ $I_{C} = 6 \text{ A}, V_{CE} = 2 \text{ V}$ $I_{C} = 6 \text{ A}, V_{CE} = 2 \text{ V}$ $I_{C} = 6 \text{ A}, V_{CE} = 2 \text{ V}$ Collector-Emitter Saturation Voltage $I_{C} = 1 \text{ A}, I_{B} = 100 \text{ mA}$ $I_{C} = 3 \text{ A}, I_{B} = 300 \text{ mA}$ $I_{C} = 1 \text{ A}, I_{B} = 100 \text{ mA}$ $I_{C} = 1 \text{ A}, V_{CE} = 2 \text{ V}$ $I_{C} = 1 \text{ A}, I_{B} = 100 \text{ mA}$ $I_{C} = 3 \text{ Collector-Emitter Saturation Voltage}$ $I_{C} = 1 \text{ A}, I_{B} = 100 \text{ mA}$ $I_{C} = 1 \text{ A}, I_{B} = 100 \text{ mA}$ $I_{C} = 1 \text{ A}, I_{B} = 100 \text{ mA}$ $I_{C} = 1 \text{ A}, V_{CE} = 2 \text{ V}$ $I_{C} = 1 \text{ A}, I_{C} = 2 \text{ V}$ GNAL CHARACTERISTICS $V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1 \text{ MHz}$	RACTERISTICSCollector-Emitter Breakdown Voltage $I_C = 10 \text{ mA}$ 25Collector-Base Breakdown Voltage $I_C = 100 \text{ µA}$ 35Emitter-Base Breakdown Voltage $I_E = 100 \text{ µA}$ 5Collector Cutoff Current $V_{CB} = 30 \text{ V}$ $V_{CB} = 30 \text{ V}, T_A = 100 ^{\circ}\text{C}$ 70Emitter Cutoff Current $V_{EB} = 4V$ 70ACTERISTICS* $I_C = 50 \text{ mA}, V_{CE} = 2 \text{ V}$ $I_C = 1 \text{ A}, V_{CE} = 2 \text{ V}$ $I_C = 6 \text{ A}, V_{CE} = 2 \text{ V}$ $I_C = 6 \text{ A}, V_{CE} = 2 \text{ V}$ $I_C = 3 \text{ A}, I_B = 100 \text{ mA}$ $I_C = 3 \text{ A}, I_B = 300 \text{ mA}$ 75Collector-Emitter Saturation Voltage $I_C = 1 \text{ A}, I_B = 100 \text{ mA}$ $I_C = 1 \text{ A}, I_B = 100 \text{ mA}$ $I_C = 1 \text{ A}, V_{CE} = 2 \text{ V}$ 75Base-Emitter Saturation Voltage $I_C = 1 \text{ A}, I_B = 100 \text{ mA}$ $I_C = 1 \text{ A}, V_{CE} = 2 \text{ V}$ 75Base-Emitter Saturation Voltage $I_C = 1 \text{ A}, I_B = 100 \text{ mA}$ $I_C = 1 \text{ A}, V_{CE} = 2 \text{ V}$ 75Output Capacitance $V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$ 75	CACTERISTICSCollector-Emitter Breakdown Voltage $I_C = 10 \text{ mA}$ 25Collector-Base Breakdown Voltage $I_C = 100 \mu A$ 35Emitter-Base Breakdown Voltage $I_E = 100 \mu A$ 5Collector Cutoff Current $V_{CB} = 30 V$ 100VcB = 30 V, V_B = 30 V, T_A = 100°C10Emitter Cutoff Current $V_{CB} = 4V$ 100ACTERISTICS*DC Current Gain $I_C = 50 \text{ mA}, V_{CE} = 2 V$ 70 $I_C = 1 A, V_{CE} = 2 V$ 100300 $I_C = 6 A, V_{CE} = 2 V$ 1515Collector-Emitter Saturation Voltage $I_C = 1 A, I_B = 100 \text{ mA}$ 300Base-Emitter Saturation Voltage $I_C = 1 A, I_B = 100 \text{ mA}$ 1.25Base-Emitter On Voltage $I_C = 1 A, I_B = 100 \text{ mA}$ 1.25Base-Emitter On Voltage $I_C = 1 A, V_{CE} = 2 V$ 1Collector-Emitter Saturation Voltage $I_C = 1 A, I_B = 100 \text{ mA}$ 1.25Base-Emitter On Voltage $I_C = 1 A, V_{CE} = 2 V$ 1Collector-Emitter Saturation Voltage $I_C = 1 A, V_{CE} = 2 V$ 1Collector-Emitter Saturation Voltage $I_C = 1 A, V_{CE} = 2 V$ 1Collector-Emitter Saturation Voltage $I_C = 1 A, V_{CE} = 2 V$ 1Collector-Emitter Saturation Voltage $I_C = 1 A, V_{CE} = 2 V$ 1Collector-Emitter Saturation Voltage $I_C = 1 A, V_CE = 2 V$ 1Collector CapacitanceV_CB = 1

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